2-D Capacitive Ultrasonic Transducer Array with individual through-wafer interconnects

- High density of through-wafer electrical interconnects to address array elements individually. (400µm x 400µm).
  - Front-side is solely dedicated to array elements avoiding any area loss to interconnects
  - Back-side is solely dedicated to electrical pads for flip-chip bonding.
- Very small parasitic capacitance to maximize device performance (0.25pF).

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4” wafer
Membranes that make up an ultrasonic transducer